P2.2: Epitaxial growth of LaCoO3 thin films by MBE.

T. Zhu, A. D. Lamirand, C. Furgeaud, C. Botella, A. Benamrouche, P. Regreny, G. Saint-Girons, R. Bachelet
Institut des Nanotechnologies de Lyon, INL-UMR5270, CNRS, Ecole Centrale de Lyon, Ecully, France

P2.6: Growth and analysis of InAs/ZnTe core-shell nanowires for superconductivity applications.

D. Mosiiets, C. W. Shum, Y.Genuist, S.Tan, J.Cibert, E.Bellet-Amalric, S.M.Frolov, M.Hocevar
University Grenoble-Alpes, CNRS, Grenoble INP, Institut Néel, Grenoble, 38000, France
Department of Physics and Astronomy, University of Pittsburgh, Pittsburgh, USA
NanoScale Fabrication and Characterization Facility, Petersen Institute of NanoScience and Engineering, University of Pittsburgh, Pittsburgh, USA
Department of Electrical and Computer Engineering, University of Pittsburgh, Pittsburgh, USA
University Grenoble-Alpes, Grenoble INP, CEA-IRIG, PHELIQS, Grenoble, 38000, France.

P2.8: Growth of MoS2 on GaN/Sapphire Substrates Using Molecular Beam Epitaxy.

Z. Bouyid, M.T. Dau, I. Florea, P. Vennéguès, J. Brault, S. Vézian, A. Michon, Y. Cordier, P. Boucaud, M. Al Khalfioui
Université Côte d'Azur, CNRS, CRHEA, Valbonne, 06560, France

P2.10: High electron mobility in in-plane InAs/GaSb core-shell nanowires: growth, characterization, and magneto-transport properties.

W. Khelifi, C. Coinon, M. Berthe, G. Patriarche, H. Sellier, X. Wallart, B. Grandidier and L. Desplanque
Univ. Lille, CNRS, Centrale Lille, Univ. Polytechnique Hauts-de-France, Junia-ISEN, UMR 8520 - IEMN, F-59000 Lille, France
Univ Rennes, CNRS, IPR (Institut de Physique de Rennes), UMR 6251, F-35042 Rennes, France
Université Paris-Saclay, CNRS, Centre de Nanosciences et de Nanotechnologies, F-91120, Palaiseau, France
University Grenoble Alpes, CNRS, Institut Néel, 38000 Grenoble, France

P2.12: Hysteresis β⇔β' phase transition in the In2Se3 film.

S. Ponomarev, D. Rogilo, N. Kurus, V. Golyashov, A. Mironov, A. Milekhin, D. Sheglov, A. Latyshev
Rzhanov Institute of Semiconductor Physics SB RAS, Novosibirsk, Russia
Novosibirsk State University, Novosibirsk, Russia

P2.14: InAs/GaAs Heterostructure Nanowires with Phase-Change Materials for Single-Photon Sources.

B. Viollet, J. Bleuse, H. Tlili, L. Cagnon, J. Claudon and M. Hocevar
Univ. Grenoble Alpes, 38000 Grenoble, France
Univ. Grenoble Alpes, CNRS, Inst. NEEL, NPSC group, 38000 Grenoble, France
Univ. Grenoble Alpes, CEA, IRIG, PHELIQS, NPSC group, 38000 Grenoble, France
Univ. Grenoble Alpes, CNRS, Inst. NEEL, MNM group, 38000 Grenoble, France

P2.16: MBE-grown AlN nanowires for 235 nm LEDs realization.

C.Guérin, F. Jourdan, JL. Rouvière, G. Jacopin and B. Daudin
Univ. Grenoble Alpes, CEA, Grenoble INP, IRIG, PHELIQS, NPSC, 17 av. des Martyrs, 38000 Grenoble, France
Univ. Grenoble Alpes, Grenoble INP, Institut Néel, SC2G, CNRS, 38000 Grenoble, France.
Univ. Grenoble Alpes, Grenoble INP, CEA, IRIG, MEM, LEMMA, 17 av. des Martyrs, 38000, Grenoble, France

P2.18: Optimizing Zincblende InP nanowires morphology with embedded InAsxP1-x QDs for high emission extraction efficiency at telecom wavelengths.

G. Bucci, T. Gzyl, P. Mrowiński, A. Musiał, V. Zannier, W. Rudno-Rudziński, F. Beltram, G. Sęk and L. Sorba
Scuola Normale Superiore, 56127 Pisa, Italy

Department of Experimental Physics, Faculty of Fundamental Problems of technology, Wrocław University of Science and Technology, Wrocław, Poland
NEST Istituto Nanoscienze CNR and Scuola Normale Superiore, 56127 Pisa, Italy

P2.20: RHEED oscillation decay and signal recovery in nucleation and step flow growth.

Magnus Quaade Oddershede and Peter Krogstrup
Quantum Foundry Copenhagen
NNF Quantum Computing Programme, Niels Bohr Institute, University of Copenhagen, Denmark

P2.22: Threading and misfit dislocations study by Electron Channeling Contrast Imaging.

A. Gilbert, A. Meguekam, E. Tournié and J.-B. Rodriguez
IES, University of Montpellier, CNRS, F – 34000 Montpellier, France
Institut Universitaire de France (IUF), F-75005 Paris, France

P2.24: A Surface X-Ray Diffraction Investigation on the 2 × 1 Surface Reconstruction of Bismuth on GaAs (001).

D. A. Crackett, G. R. Bell, D. Sterland, P. J. Mousley, H. Hussain and R. D. Richards
Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield, UK
Department of Physics, University of Warwick, Coventry, UK
Diamond Light Source, Harwell Science and Innovation Campus, Didcot, UK

P2.26: Anomalous growth of epitaxial silicene on graphene : a kinetic Monte-Carlo approach.

K. Wang, M. Abel, M. Koudia, F. Fabbri, A. Michon, A. H. Denawi, H. Vach, I. Berbezier, and J.-N. Aqua
Sorbonne Université, Centre National de la Recherche Scientifique,
Institut des NanoSciences de Paris, Paris, France
Aix Marseille Université, Centre National de la Recherche Scientifique, Université de Toulon, IM2NP, Marseille, France
NEST, Istituto Nanoscienze – CNR, Scuola Normale Superiore, Pisa, Italy
CRHEA, Université Côte d'Azur, CNRS, Valbonne, France
LPICM, CNRS, École Polytechnique, Palaiseau, France

P2.28: Controllable Branching of Self-Catalysed AlGaAs Nanowires Synthesised via Molecular Beam Epitaxy.

Giorgos Boras, Haotian Zeng, Raghavendra Juluri, Stephen Church, Huiwen Deng, Hui Jia, Anton Velychko, Chong Chen, Ziyue Yin, Mingchu Tang, David Mowbray, Patrick Parkinson, Ana M. Sanchez, Huiyun Liu
Department of Electronic and Electrical Engineering, University College London, WC1 E7J, United Kingdom
Department of Physics, University of Warwick, Coventry CV4 7AL, United Kingdom
Department of Physics and Astronomy and the Photon Science Institute, University of Manchester, M13 9PL, United Kingdom
Department of Physics and Astronomy, University of Sheffield, S3 7RH, United Kingdom

P2.30: Drastic enhancement of the internal quantum efficiency of thick (In,Ga)N layers by thermal annealing.

J. Kang, A. Campbell, J. Lähnemann, L. Geelhaar, and O. Brandt
Paul-Drude-Institut für Festkörperelektronik, Leibniz-Institut im Forschungsverbund Berlin e.V., Hausvogteiplatz 5–7, 10117 Berlin, Germany

P2.32: Influence of High-temperature annealing on MBE–grown AlN thin film layers.

S. Mitra, J. Brault, M. Nemoz, A. Courville, and J-V.Duboz
Université Côte d'Azur, CNRS, CRHEA, 06560 Valbonne,France

P2.34: Kinetic monte carlo simulation of GaAs growth on (001) silicon.

M. Silvestre, A. Gilbert, J.-N. Aqua, E. Tournié, J.-B. Rodriguez
IES, University of Montpellier, CNRS, F – 34000 Montpellier, France
RIBER SA, F – 95870 Bezons, France
Sorbonne Univ, CNRS, Inst. Nanosci. Paris, INSP, F-75005 Paris, France
Institut Universitaire de France (IUF), F-75005 Paris, France

P2.36: Segregation-Driven Formation of Bismuth Quantum Dots in GaAsBi Layers and Quantum Structures.

Butkutė Renata, Špokas Aivaras, Zelioli Andrea, Vaitkevičius Augustas , Bičiūnas Andrius , Dudutienė Evelina , Čechavičius Bronislovas, Skapas Martynas , Čerškus Aurimas, Talaikis Martynas, Baranowski Piotr, Wojnar Piotr
Center for Physical Sciences and Technology, Vilnius, Lithuania
Institute of Photonics and Nanotechnology, Vilnius University, Vilnius, Lithuania
Institute of Physics, Polish Academy of Sciences, Warsaw, Poland

P2.38: Surface processes on Bi2Se3(0001) during indium deposition studied by in situ reflection electron microscopy.

D. Rogilo, S. Ponomarev, D. Nasimov, K. Kokh, A. Ryabishchenkova, V. Golyashov, D. Sheglov, A. Latyshev
Rzhanov Institute of Semiconductor Physics SB RAS, Novosibirsk, Russia
Novosibirsk State University, Novosibirsk, Russia
Sobolev Institute of Geology and Mineralogy SB RAS, Novosibirsk, Russia

P2.40: Tuning the Diameter of GaAs Nanowires by Wet Chemical Etching. J.Pelenc , P. Regreny, C. Botella, N. Blanchard, N. Chauvin, and J. Penuelas,
Ecole Centrale de Lyon, CNRS, INSA Lyon, Université Claude Bernard Lyon 1, CPE Lyon, INL, UMR 5270, 69130 Ecully, France
University of Lyon – CNRS, ILM, UMR 5306, Université Lyon I, Bât. A. Kastler, 10 rue A.Byron, 69622 Villeurbanne, France

P2.42: Growth of Superconducting Sr2RuO4 Thin Films via Thermal Laser Epitaxy.

Faeth Brendan, Harbola Varun, Hensling Felix, Majer Lena, Schwaigert Tobias, Wu Yu-Mi, Van Aken Peter, Suyolcu Eren, Braun Wolfgang, Mannhart Jochen
Max Planck Institute for Solid State Research, Germany
Epiray GmbH , Germany
Cornell University, New York, United States

P2.44: Optimizing thermal management of equipment used in MBE/PVD-processes via simulation.

T. Stiller, I. Nitsche, S. Krinke, A. Ludwig, and A. Wieck
CreaTec Fischer & Co. GmbH, Erligheim, Baden-Würtemberg, Germany
Ruhr Universität Bochum, Bochum, Nordrhein-Westfalen, Germany